

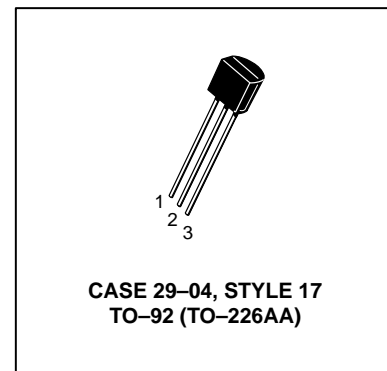
High Current Transistors

NPN Silicon

BC489, A, B

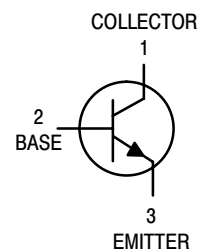
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	80	Vdc
Collector–Base Voltage	V_{CBO}	80	Vdc
Emitter–Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	0.5	Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 10 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	80	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	80	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	—	100	nAdc

ON CHARACTERISTICS*

DC Current Gain ($I_C = 10 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}$)	BC489 BC489A BC489B	h_{FE}	40	—	—	—
($I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc}$)*			60	—	400	—
			100	160	250	—
			160	260	400	—
			15	—	—	—

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle 2%.

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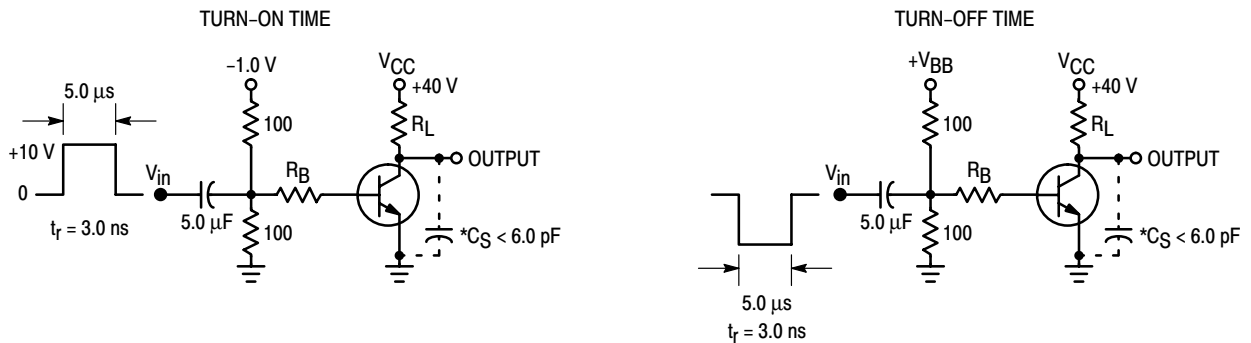
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS* (Continued)					
Collector–Emitter Saturation Voltage ($I_C = 500\text{ mA dc}$, $I_B = 50\text{ mA dc}$) ($I_C = 1.0\text{ A dc}$, $I_B = 100\text{ mA dc}$)	$V_{CE(sat)}$	—	0.2 0.3	0.5 —	Vdc
Base–Emitter Saturation Voltage ($I_C = 500\text{ mA dc}$, $I_B = 50\text{ mA dc}$) ($I_C = 1.0\text{ A dc}$, $I_B = 100\text{ mA dc}$) ⁽¹⁾	$V_{BE(sat)}$	—	0.85 0.9	1.2 —	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 50\text{ mA dc}$, $V_{CE} = 2.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	—	200	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	7.0	—	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ib}	—	50	—	pF

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle 2.0%.



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

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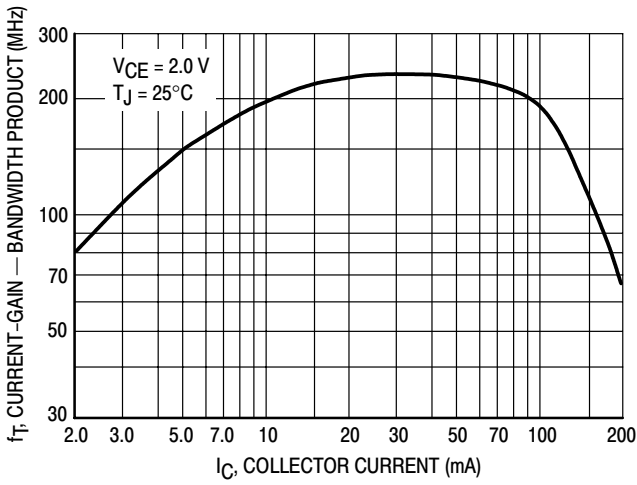


Figure 2. Current-Gain — Bandwidth Product

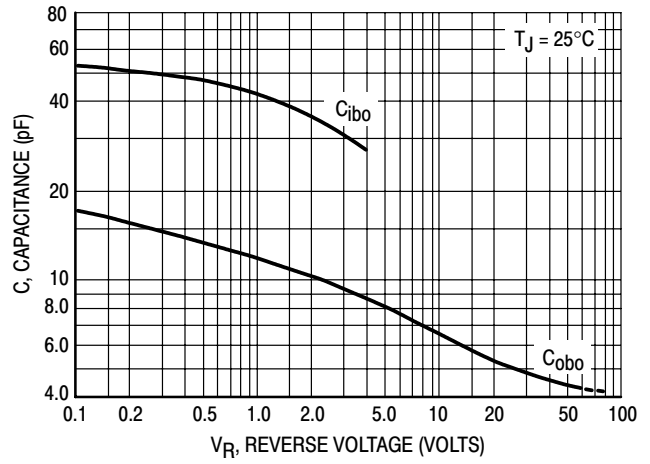


Figure 3. Capacitance

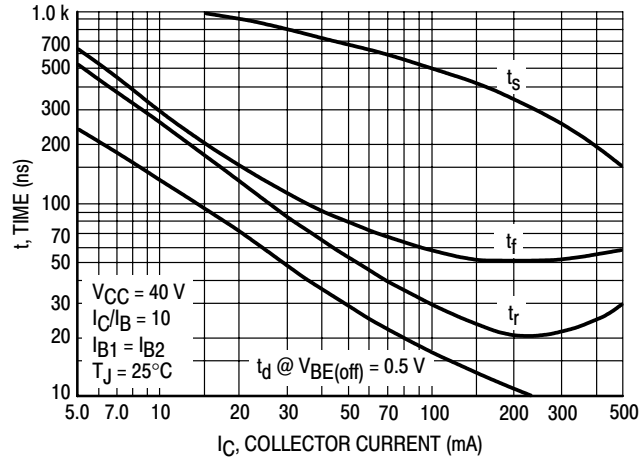


Figure 4. Switching Time

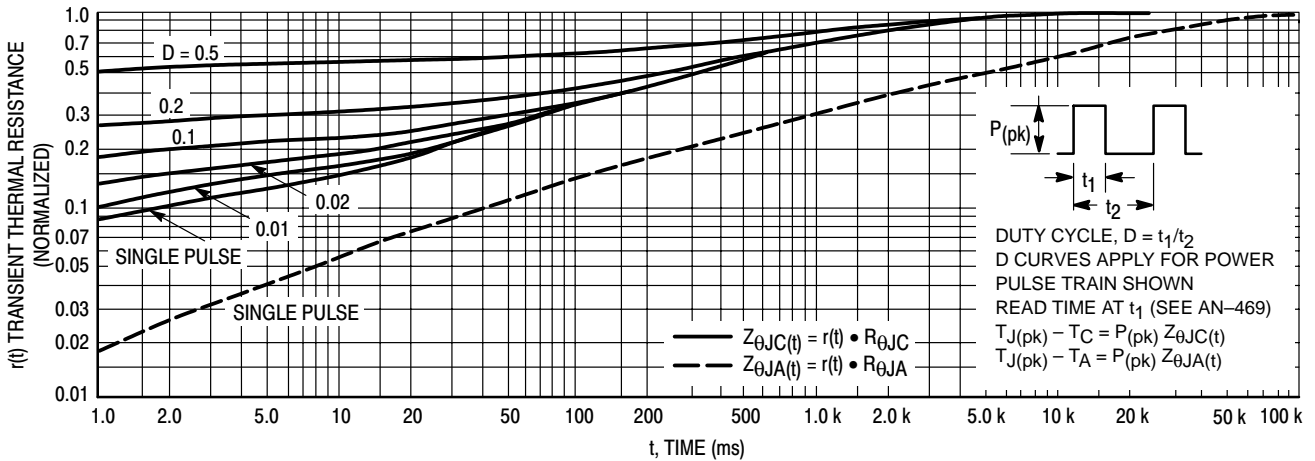


Figure 5. Thermal Response

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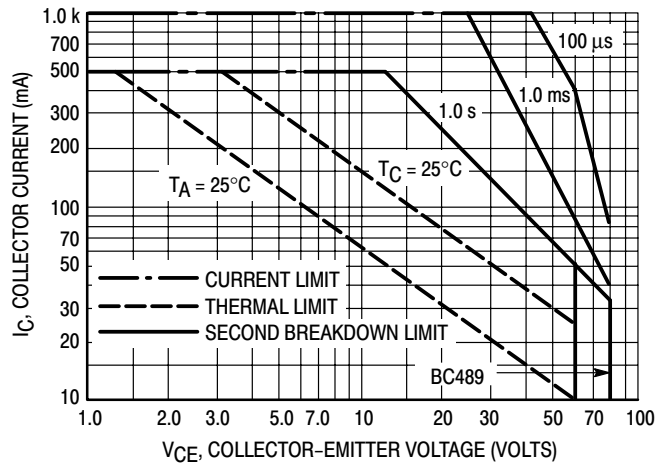


Figure 6. Active Region — Safe Operating Area

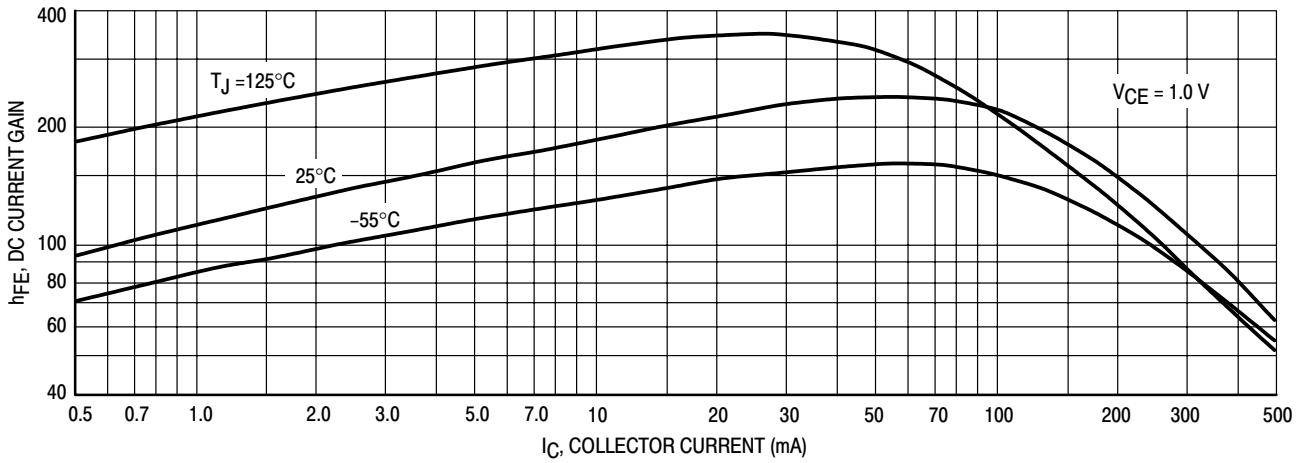


Figure 7. DC Current Gain

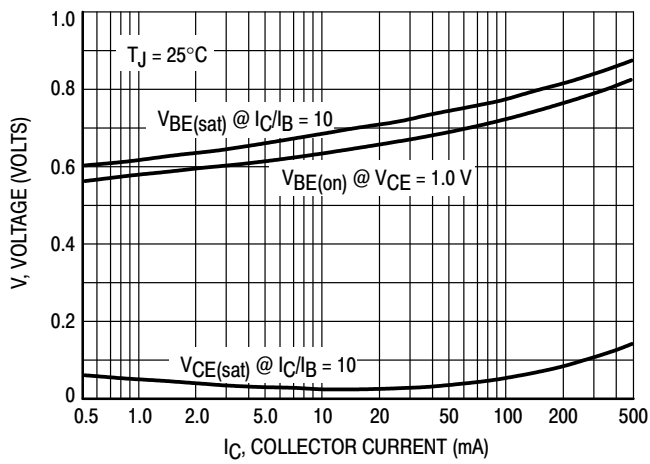


Figure 8. "On" Voltages

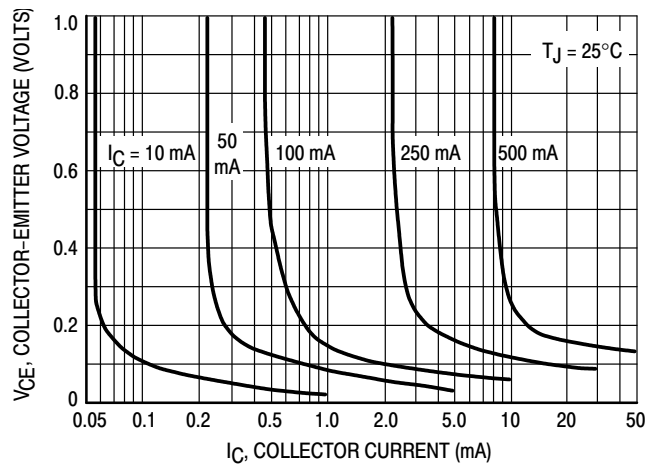


Figure 9. Collector Saturation Region

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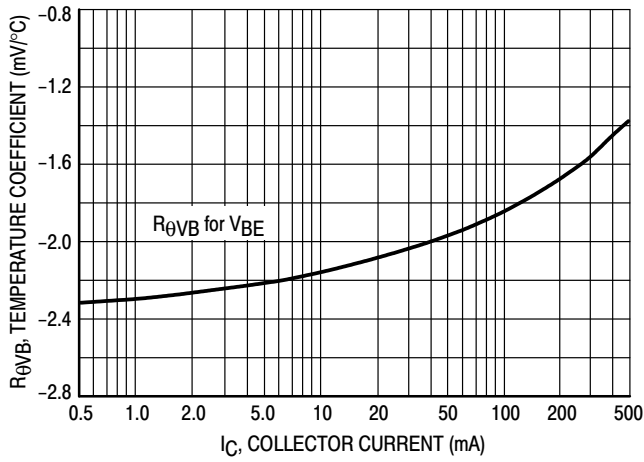


Figure 10. Base-Emitter Temperature Coefficient

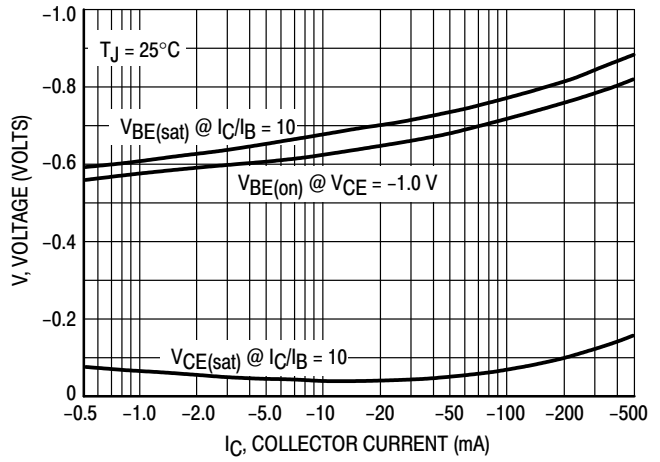


Figure 11. "On" Voltages

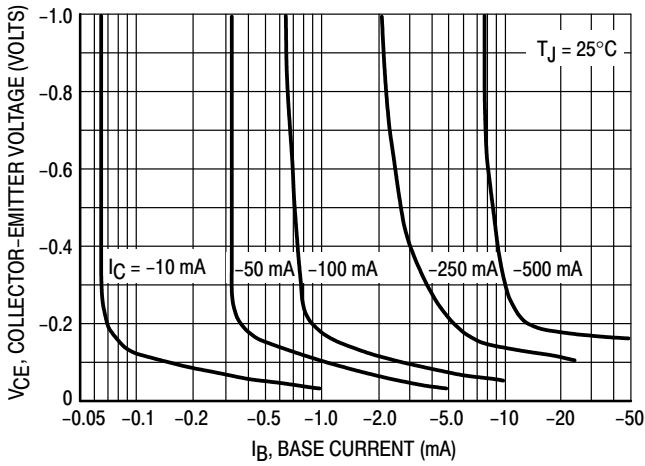


Figure 12. Collector Saturation Region

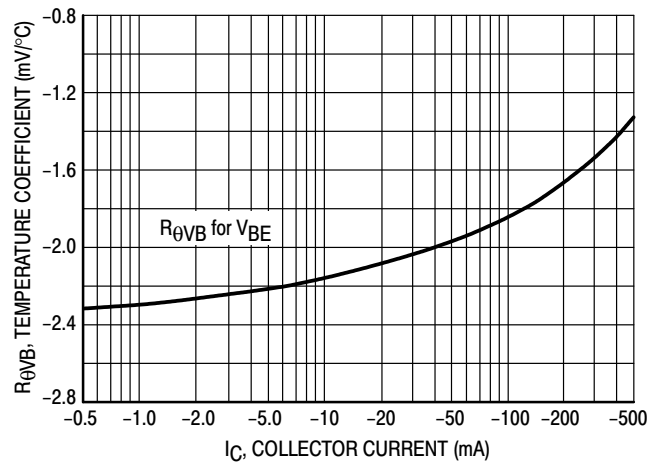
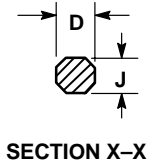
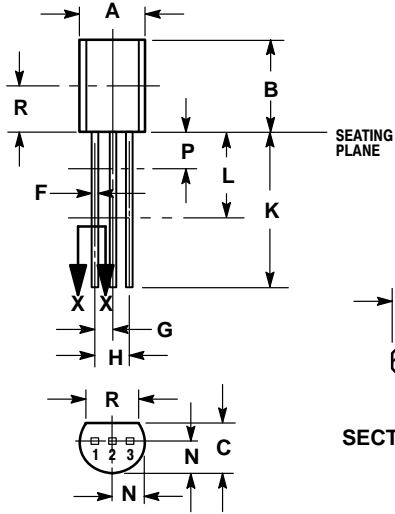


Figure 13. Base-Emitter Temperature Coefficient

BC489, A, B

PACKAGE DIMENSIONS

CASE 029-04
(TO-226AA)
ISSUE AD



STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

Notes

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